

**AN1831**  
**Application Note**  
**MSCSICSP3/REF2 SiC SP3 Module Driver Reference Design**

Final  
October 2018



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# 1 Revision History

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The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

## 1.1 Revision C

Revision C was published in October 2018. In Revision C of this document, the following changes were made:

- Updated the [Quickstart \(see page 15\)](#) subsection.
- Added the [Full Setup with a Module and DC Bus Power \(see page 15\)](#) subsection.
- Updated the [Block Diagram \(see page 2\)](#) in the [Introduction](#) section.

## 1.2 Revision B

Revision B was published in May 2018. In Revision B of this document, the following changes were made:

- Added maximum output current in the [Reference Design Description \(see page 4\)](#) section.
- Added maximum output current description to Electrical Limits table in the [Electrical Characteristics \(see page 14\)](#) section.

## 1.3 Revision A

Revision A was published in May 2018. It was the first publication of this document.

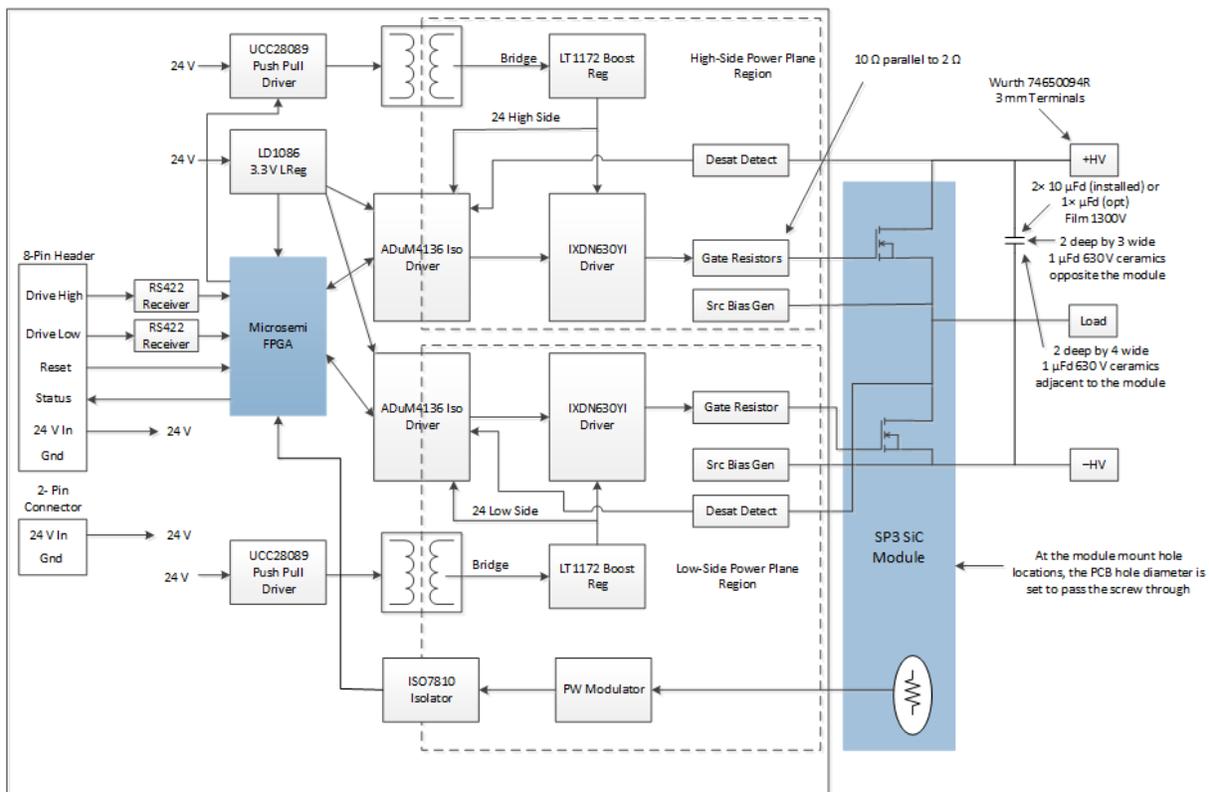
## 2 Introduction

This [reference design](#) provides an example of a highly isolated SiC MOSFET dual-gate driver for the SP3 SiC phase leg modules. It can be configured by switches to drive in a half bridge configuration with only one side on at any time and with dead time protection. It can also be configured to provide concurrent drive, if necessary. This design is intended for use with Microsemi SiC SP3 modules. The dead time and gate drive resistance are adjusted by the user to match the requirements of the application. Optional dead time protection and optional desaturation protection makes device evaluation easier while lowering the risk of damaging parts.

In this document, you will find a quick start guide in addition to useful reference information, including the bill of materials and schematics. The Gerber files, Verilog code, and the Libero project are available at [Microsemi.com](http://Microsemi.com) product page.

This design is offered as an engineering tool for the evaluation of Microsemi SP3 SiC modules in a laboratory environment. It has not been tested at voltage across the insulation boundaries. It is the responsibility of the engineer to use the proper safety equipment and procedures. Reference the appropriate UL or IEC standards for guidance on insulation and creepage requirements.

**Figure 1 • Block Diagram with Half Bridge**



When comparing the drive of Si devices against SiC devices there are two important differences to consider:

- The slew rate at the output of a SiC half bridge can be much higher than with silicon. SiC power stages can easily achieve a  $dV/dt$  of 50 kV/ $\mu$ s or more. This affects the design of the gate drive signal isolation and EMI mitigation. It creates potential issues with the method of implementation of parts of the system such as the gate power DC-DC function. The intention of this board is to provide an off-the-shelf test solution which addresses these issues.

- SiC MOSFETs are normally driven at higher asymmetrical gate voltages compared to silicon MOSFETs. Typical drive levels are  $-5\text{ V}$  to  $20\text{ V}$ . The driver can be configured to a lower drive level of  $-5\text{ V}$  to  $18\text{ V}$  if the resulting higher  $R_{\text{ON}}$  is acceptable. Reference [Microsemi Application Note 1826](#) for additional gate drive recommendations.

## 3 Reference Design Description

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This reference design is optimized to drive SP3 SiC MOSFET devices at high speeds with desaturation protection. It is a base design that can be simplified depending upon the individual system requirements. The following is a list of features:

- Requires only a 12 V power input
- –5 V, 20 V output gate drive, jumper selectable to –5 V, 18 V
- Includes an example of temperature monitoring
- Galvanic isolation of more than 2000 V on both gate drivers<sup>1</sup>
- Capable of 16 W of gate drive power/side
- Peak gate current of up to 30 A
- Maximum output current of approximately 60 A due to trace limitations
- Maximum switching frequency greater than 400 kHz<sup>2</sup>
- Single-ended or RS485/RS422 differential input gate control
- Shoot through (short-circuit) protection
- $\pm 100$  kV/ $\mu$ s capability
- Programmable dead time protection
- Fault signaling
- Under voltage lockout protection

### Notes:

1. The ICs and transformer are rated to greater than 2000 V. The trace clearance rating is dependent upon the allowable contamination level and is the responsibility of the user. Note that the board clearance around the gate transformers is low for a 2 kV design. An epoxy coating should be added to adjacent trace if additional protection is desired.
2. The board has been tested to 400 kHz. Any calculation of gate-power drive must include the frequency dependent portion of the driver IXDN630 and the ADuM4136.

### 3.1 Gate Drive

This design uses Analog Devices ADuM4136 to pass signals across the isolation boundary. An IXDN630 driver is then used to increase the output drive current to 30 A, something more in line with the current associated with a module. A Zener diode is added in the positive leg of the ADuM4136 to increase the UVLO trip point to approximately 18 V.

There is a need to transfer energy across the isolation interface to drive the gates. Most standard isolation supplies are not designed with adequate insulation, a low capacitance interface and tolerance to the high dV/dt associated with SiC MOSFETs in a half bridge. Consider that 10 pF of capacitance across the barrier translates to a 350 mA current spike back into the gate supply and its associated grounding at 35 V/ns. It is desirable to keep the capacitance across the gate supply transformer to a minimum.

The transformer used in this design has a few pF capacitances. Other designs can be considered and higher capacitance can be tolerated. However, it is important to keep in mind that the displacement current across the transformer winding must be absorbed by the drive FETs into the source sense resistors and from the low voltage ground into the system environment.

This driver has capacitors from the low voltage (SELV) side ground to the screw holes. This provides a means by which the currents can be directed to a chassis or other ground reference. Without this grounding, the displacement currents are directed into the RS422 pairs, possibly resulting in excessive common-current mode or failure of the signal interface.

Power is transferred across the isolation boundary with a UCC28089 push-pull driver and FDS3512 MOSFETs, followed by a custom transformer. Power is transferred unregulated over the boundary and then regulated on the gate side. This decouples the isolation transformer design from the regulator design.

A Microsemi FPGA controls power sequencing. If at any time a fault is flagged by one of the ADuM4136 drivers, then switching is cut off to both drivers. This may help the power stage survive output device failures or at least lead to less damage.

The gate power transformer is constructed from an RM10 core (Epcos B65813J0000R041) and split bobbin (Epcos B65814N1012D002). The wire is by Belden (part number 8051; double insulated magnet wire). The primary is 12 turns center tapped, 22 gauge. The secondary is 12 turns, 22 gauge. The pins on the bobbin are not used. Instead, the pins are pulled. The resulting hole is then drilled to pass the 22 gauge wire. This results in a cleaner construction than what would occur by wrapping the wire on the pins, as is normally done.

## 3.2 Gate Resistor Selection

Gate resistor selection is driven by a number of factors, including the following:

- Lower resistance results in lower switching loss.
- Gate resistance that is too low results in excessive ringing.
- The gate OFF drive should be roughly 2:1 greater than the ON drive to avoid excessive Miller Effect conduction from the bump on the opposing transistors.
- Modules that drive at a high frequency have a relatively high gate resistor power dissipation. Heat sinking of the resistors may be necessary.
- If desaturation protection is being considered, there may be a need to turn OFF slowly. This is more applicable to product development where it may be acceptable to take the additional switching loss.

This board is provided with three parallel 10  $\Omega$  resistors that provide ON and OFF drive, 3.3  $\Omega$ , and two parallel 10  $\Omega$  resistors that provide only OFF drive through a diode resulting in 2  $\Omega$ .

## 3.3 Desaturation Protection

In a general sense, desaturation protection is provided as an attempt to protect the power module in the event of an over-current condition normally due to a loss of control or failure of the opposing device. If an over-current condition results in a device going out of saturation when the gate is commanded ON, then the device is commanded permanently OFF. Sometimes it is desirable to have this function during product development even if it will not be used in the final product.

Setting up properly operating desaturation protection is tricky. Desaturation events generally result from excessive drain current. In an over-current event, the inductive kick on the drain is higher than normal. A technique around this is to shut off the transistor slowly. Note that this does not protect in the event the command to turn OFF happened to occur just below the desaturation point. In addition, at the higher currents of modules, it becomes more difficult to provide a bus structure with a proportionally lower inductance. For this reason, the function is not used in many cases.

The resistors on this driver should be set such that the turn-ON drive current is less than the turn-OFF drive current. The ratio of the currents normally is about 2:1 to avoid Miller Effect conduction. This is not a precise number and closer to 1:1 is fine in many applications. If testing shows there is a sufficient margin on the breakdown voltage during an over-current event, then the desaturation circuitry can be considered.

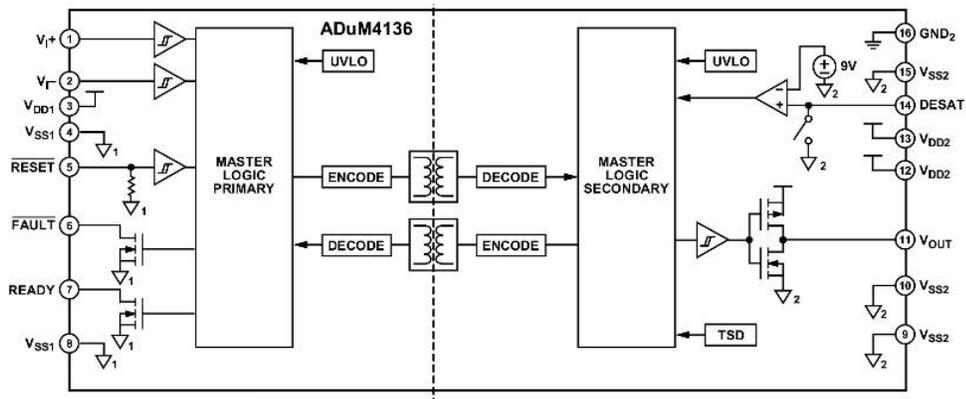
The top-side and bottom-side drivers are identical. The top-side driver desaturation circuit is described here. The artwork is setup such that two series high-voltage diodes can be considered (D29 and D30). The printed circuit board (PCB) is assembled with one RP1HV1 fast recovery diode. During switching, the diode capacitance (about 2 pF) drives current into the SBD clamp diodes (D9 and D10). R31 sets the forward current in the D29 and D30 diodes. Reference the ADuM4136 specification for information on setting up the circuit. It is important to consider the following:

- If desaturation detection is not used, D32 should be shorted.
- If desaturation detection is used, then D32 is recommended. If D32 is not installed, then R32 should not be less than the 220  $\Omega$  in the circuit. This is to avoid latching U7 due to excessive current in a diode internal to U7 that parallels D32.
- If D32 is installed, it is important to be sure that the average switching current carried by D32 does not rise to a level high enough that it collapses the Zener negative gate-voltage supply.

When a gate high is asserted, it is expected that within a few hundred ns the source-to-drain voltage across the power FET will be low. If this is not the case, then circuitry both internal and external to the ADuM4136 verifies this and shuts off the FET.

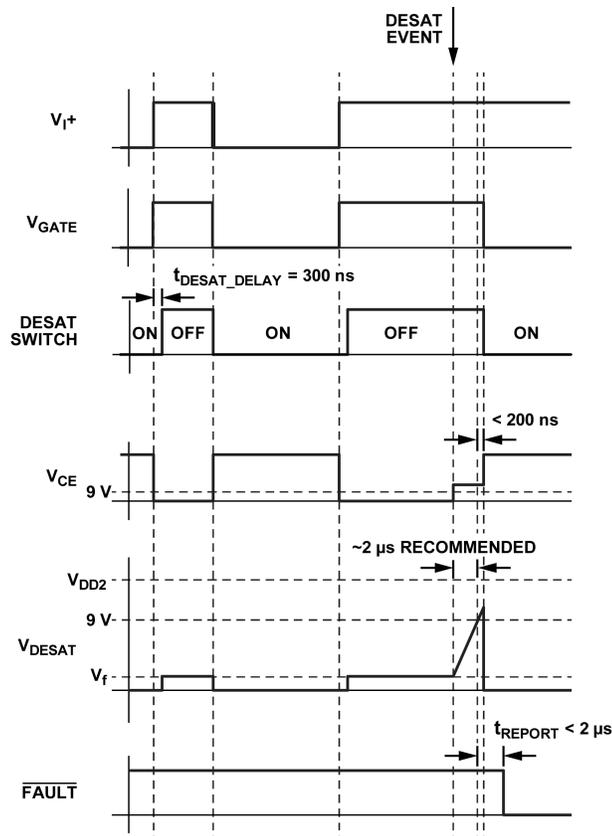
At approximately 300 ns after asserting the high-FET gate voltage, a FET internal to the ADuM4136 releases the DESAT pin. The pin is then free to float up. A 500  $\mu$ A current source pulls it up internal to the ADuM4136. In addition, a 10K resistor pulls it up externally. If it crosses 9 V, the ADuM4136 interprets the condition as a fault and shuts off FET drive. The FET gating the DESAT pin is at the switch in the upper right of the following block diagram (note that the grounds on the primary and secondary sides are isolated from each other).

**Figure 2 • ADuM4136 Block Diagram**



SiC MOSFETs have a much smaller die than their silicon counterpart. As a result they have lower thermal mass and heat faster in a short circuit condition. The following figure is from the ADuM4136 spec showing timing typical of an IGBT. With SiC MOSFETs, a delay of 200 ns–300 ns would be more appropriate than 2  $\mu$ s delay.

Figure 3 • ADuM4136 Spec



The delay time is controlled by R31 and C17. ADuM4136 has a blanking time of 300 ns, which should be enough for a SiC power stage in most cases. The additional delay past blanking can be increased by adding C17 or decreased slightly by reducing R31. If a scope is used to observe the desat signal at the input to the ADuM4135, the low-side driver should be observed and a very low capacitance probe should be used.

### 3.4 Thermistor Support

This board demonstrates a method by which the module thermistor can be brought back to a processor in a safe and relatively simple manner. In the event of a catastrophic failure of the module, there is the possibility a plasma within the device could touch the thermistor. If the thermistor directly interfaces with the control structure, this would result in power from the DC bus feeding back into the low-voltage control structure. To prevent this, the thermistor information is captured in the environment of the low-side driver. U12 then passes back a pulse width modulation (PWM) signal across the insulation boundary.

The thermistor resistance is converted to a PWM signal by U11. U11A is an oscillator that generates a triangular-like wave between 1/3 and 2/3  $V_{\text{CC}}$ . In this case,  $V_{\text{CC}}$  is 3.3 V from PS2. U11B then compares the oscillator with the level from the thermistor, resulting in a PWM input to U12.

The PWM output normally would be linearized by a remote processor. The current implementation of the FPGA does not process the signal. However, the signal can be observed at the feed through next to C59. See Figure 5 (see page 13) for the location.

It is common practice to map the response of a thermistor to the temperature through a look-up table. The interface circuit provided adds another layer of non-linearity. This adds another calculation in the generation of the look-up table. With the ramp limits at  $1/3$  and  $2/3 V_{CC}$ , the circuit captures over a 4:1 range of thermistor resistance. This can be extended as described below.

### 3.5 Thermistor Transfer Function

This section describes the transfer function of the voltage at the thermistor to the duty factor observed by the FPGA/processor. These equations are provided without proof. Define the following variables:

- $D$  = duty factor. It ranges from 0 to 1.
- $V_x$  = thermistor voltage. This is expressed as a ratio of  $V_{CC}$ . In the circuit provided,  $V_x$  can be measured between values of  $1/3$  (0.333) and  $2/3$  (0.666)
- Variables  $A$ ,  $B$ ,  $C$  are temporary variables to simplify expressions.

At the high-temperature measure limit,  $V_x = 1/3$  and  $D = 1$ . Likewise at the low-temperature measure limit,  $V_x = 2/3$  and  $D = 0$ .

The equation that maps  $V_x$  to  $D$  is as follows:

$$A = \ln((1 - V_x)/V_x);$$

$$B = 2 * \ln(2);$$

$$D = \frac{1}{2} + A/B;$$

The inverse equation mapping  $D$  to  $V_x$  is as follows:

$$C = (2 * D - 1) * \ln(2);$$

$$V_x = 1/(1 + \exp(C));$$

The resistor  $R67$  sets the resistance at which the thermistor resistance maps to  $V_x = 0.5$ , which defines the center of the measure range. Resistors  $R47$ ,  $R64$ , and  $R65$  set the oscillator ramp limits at  $1/3 V_{CC}$  and  $2/3 V_{CC}$ .

It may be desired to increase the measure range of the circuit beyond the 4:1 range provided. Again provided without proof, if  $R47$  and  $R64$  are increased such that the oscillator limits are  $(k - 1)/k * V_{CC}$  and  $(1/k) * V_{CC}$ , then substitute  $\ln(2)$  with  $\ln(k - 1)$  in the above equations.

As the circuit is provided,  $k = 3$ . This assumes  $R47 = R64$ . Lowering  $R65$  instead is okay as long as the output impedance of  $U11$  is not significant and the additional current demand is not significant. As an example, if  $R47$ ,  $R64 = 50K$  and  $R65 = 10K$ , then the oscillator ranges from  $0.142 V_{CC}$  to  $(1 - 0.142) V_{CC}$ . Then  $k = 1/0.142 = 7$ . Substitute  $\ln(6)$  in the above equations.

### 3.6 High-Current Connections and Structure

The SP3 Driver Reference Board comes with ceramic capacitors installed opposite the module and adjacent to the module. It also comes with two  $10 \mu F$  four-lead film capacitors installed on the side opposite the module. It does not include bus snubbing. Bus snubbing along with the gate drive resistors are left for the customer to define.

As with any high-power module, the SP3 module requires gate drive circuitry that normally is fabricated on the PCB with fine geometry trace but it also requires high-current capability. This PCB is a compromise to demonstrate the module but is not capable of carrying the module's full current. It is fabricated with four layers of 2 oz. copper without thermal relief. The PCB is capable of 60 A with approximately a  $30 \text{ }^\circ\text{C}$  temperature rise. Testing of the board was done using 2 mm thick copper terminal connected to a 6.8 gauge flat braid wire.

A better PCB structure would be 3 oz.–4 oz. copper on the outside and 4 oz. on the inside with thermal relief. A PCB constructed in this manner would probably require pre-heating to rework due to the high thermal capacity of the PCB.

### 3.7 Reduced Gate Voltage Operation

In some applications, it may be desirable to reduce the gate drive voltages. The gate drive voltages are controlled by two circuits. The following table describes this relationship.

**Table 1 • Reduced Gate Voltage Operation**

Parameter	High-side Driver	Low-side Driver
Total voltage 25 V typical	R37, R38, R39	R82, R83, R84
Negative gate drive voltage	D13	D23

Note that resistors set the total voltage (25 V typical). Also, note that the total voltage is set by a boost regulator and the negative gate drive is set by Zener diode regulators.

Example: assume a  $-3$  V/18 V drive is desired. The Zener diodes should be replaced with 3 V Zeners (SZBZ84C3VOLT1G would be a good candidate). In addition, the total drive voltage should be reduced from 25 V to 21 V. This is outside of the adjustment range using R37 and R82, so R39 and R84 should be replaced with a value roughly 4K lower (around 16.5K).

There are two things to be aware of when doing this. The first is that the LT1171 boost regulator input voltage must be below the output voltage in order to maintain regulation. With this change, the nominal input voltage should be considered 11 V instead of 12 V without a change to the transformer. The second thing is that the Zener diode used to set the negative gate drive, like any Zener regulator, can be loaded down by excessive loading. The most common cause of excessive loading is an improperly configured desaturation circuit and a module with gate loading due to a damaged gate structure.

## 4 Firmware

The default firmware is configured by switches for two modes:

1. The upper and lower drivers act independently. This function allows the drive signal to propagate through immediately. There is no dead time protection.
2. Only one ON (half-bridge mode). With this mode, there is a switch-programmable dead time. Dead time is programmable in 100 ns steps up to 3.1  $\mu$ s.

A switch selects between a "one-input mode" and a "two-input mode." "One-input mode" makes it unnecessary to program dead time into a source-pulse generator. The use of the FPGA to generate dead time makes it unnecessary to program the dead time into an external generator.

Internal logic is all driven by a 10 MHz clock. Inputs are quantized to the 10 MHz clock in half-bridge mode. The quantization to the clock makes the hold-off logic immune to input noise. However, it means that there will be timing jitter in the signal propagated through the FPGA.

**Table 2 • Configuration Switch Settings**

Switch	Function
1	Switch On, signal low—2 input mode: pins 1,2 to low side; pins 6,7 to high side Switch Off, signal high—1 input mode (pins 1,2)
2	Switch On, signal low—80 kHz mode Switch Off, signal high—external input mode
3	Switch Off, signal high—one drive only, synchronous mode with dead time Switch On, signal low—independent drive, asynchronous mode
4	Dead time select Switch On, signal low = no delay Switch Off, signal high = 1600 ns
5	Dead time select Switch On, signal low = no delay Switch Off, signal high = 800 ns
6	Dead time select Switch On, signal low = no delay Switch Off, signal high = 400 ns
7	Dead time select Switch On, signal low = no delay Switch Off, signal high = 200 ns
8	Dead time select Switch On, signal low = no delay Switch Off, signal high = 100 ns

The FPGA is a Microsemi Igloo AGL030V2-VQ100. A Microsemi Flashpro 5 or Flashpro 4 programmer can be used to program the device. Other devices have not been tested. The project is in Verilog using Libro SoC. Information on IGLOO FPGAs can be found at <http://www.microsemi.com/product-directory/fpgas/1689-igloo>.

Switch 1 is closest to the FPGA. Common switch settings are as follows:

**Table 3 • Common Switch Settings**

Mode	Sw1	Sw2	Sw3	Dead Time
80 kHz demo	Don't care	ON	ON	Yes
2 input	ON	OFF	ON	Yes
1 input on high-side input only	OFF	OFF	ON	Yes
Independent	ON	OFF	OFF	Not App

SiC MOSFETs require very little dead time. Generally, dead time corrects for the delays associated with output switching of gate driver skew (the time it takes to drive the gate) and the recovery of the power device. With SiC MOSFETs, there is no recovery time. In addition, the ADuM4136 is a very low skew driver. A minimum dead time of 100 ns is possible in most applications. This is programmed with SW4 through SW7 ON, SW8 OFF.

## 4.1 Layout Considerations

This design was done in KiCad. KiCad is not a preferred tool for high-voltage layouts due primarily to limitations with the design rules. This design was done with the following general guidelines.

The gate power supply cores are conductors. Appropriate creepage should be observed around the core on the component side.

The placement of the IXDN630 gate driver and all trace are designed to minimize drive inductance. This includes trace width, multiple feed-throughs, and the placement of all components involved with the nets that carry the high-gate current pulses.

The thermistor is sensed within the environment of the low-side driver. This is to provide isolation from the low-voltage (SELV) environment, but at the same time not place it in the environment of the high-side driver and its associated  $dV/dt$ .

The thermistor trace passes over nets that are not subject to the high  $dV/dt$  of the high-side driver.

The desaturation detection diodes bridge the plane environments of the two sides of the diodes. This allows the use of series-connected diodes. UIS capable diodes are preferred with series-connected diodes.

The output nets must carry the rated current and have the proper creepage.

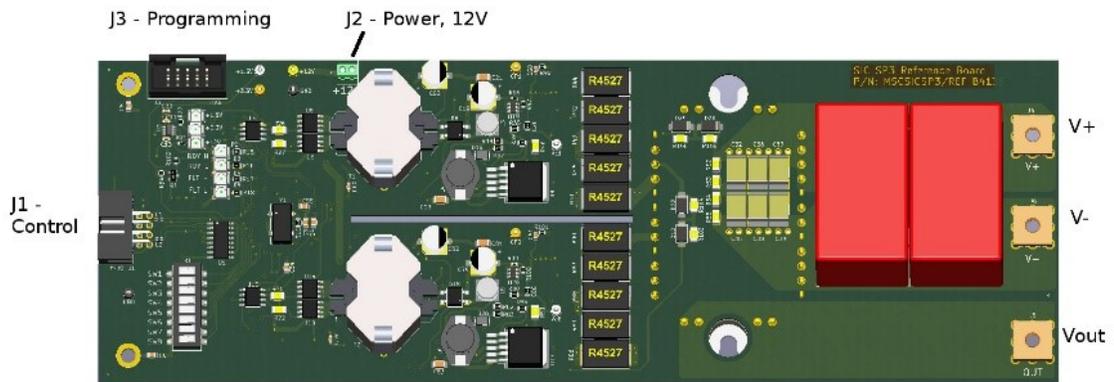
## 5 IO and Settings

This section describes the IO and settings for the SP3 driver reference design.

### 5.1 Connectors

The following image shows the placement of important connectors on the board.

**Figure 4 • Connectors**



Connector J1 is an eight-pin male header with the following pinout:

**Table 4 • J1, Control Connector Pinout**

Pin	Signal	Condition
1	Drive high +	True will turn ON the high-side FET. Depending upon switch SW0 it can also control the low side.
2	Drive high –	
3	Reset	A high (3.3 V logic) input asserts reset to the ADuM4135. Pulled down through 10K on the board.
4	Ground	Signal ground. Optionally power ground.
5	Drive low +	Depending upon switch SW0 turns ON the low-side FET
6	Drive low –	
7	Status	Fault output (3.3 V logic with 1K source resistance)
8	Power	12 V input

Connector J2 is an alternate power connector.

**Table 5 • J2, Alternate Power Connector Pinout**

Pin	Signal
1	12
2	Gnd

Connector J3 is the programming connector. The connector pinout follows that of the Microsemi Flashpro programmers.

## 5.2 LEDs and Gate-Voltage Adjustments

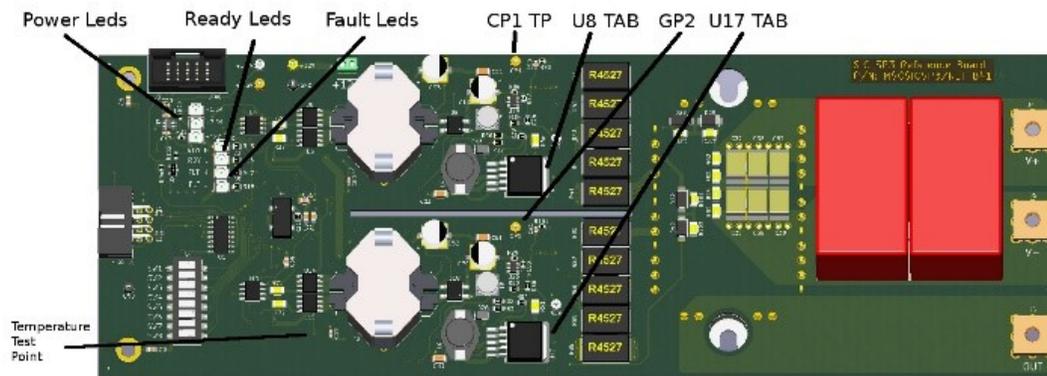
Three power LEDs indicate the presence of 12 V, 3.3 V, and 1.5 V core voltage. Two LEDs labeled “RDY H” and “RDY L” indicate the current status of the ready signal from the two ADuM4136 drivers. Two LEDs labeled “FLT H” and “FLT L” indicate the current status of the fault signal from the ADuM4136 drivers.

The following table shows how the LEDs respond. The status of the high-side interface and low-side interface display separately.

**Table 6 • J1, Control Connector Pinout**

Ready	Fault	Condition
Off	Off	The secondary side is under voltage.
On	Off	Normal operating state.
On	On	Faulted due to a desaturation condition.

**Figure 5 • LEDs and Test Points**



The PCB is shipped configured for –5 V, 20 V gate drive. R82 and R37 should be shorted to yield –5 V, 18 V gate drive. Four test points are shown in the above diagram CP1 to U8 tab should be 25 V when configured for 20 V gate drive and 23 V with 18 V gate drive. U8 tab to the corresponding module source lead should measure 5 V. On the low side test point GP2 and U17 tab have the same role.

It should be noted that the board input voltage should be kept under 13 V. Otherwise, the boost regulators will conduct through and start raising the gate voltage.

## 5.3 Electrical Characteristics

In the following tables, all voltages are referenced to ground.

**Table 7 • Electrical Limits**

Description	Min	Typ	Max	Units
Supply voltage, full power	11	12	13	V
Supply current, idle		0.16	0.2	A
Supply current maximum <sup>1</sup>			3.0	A
Maximum slew rate			100	V/ns
Maximum current output			100	A

Note:

1. The driver input power is primarily dissipated in the gate resistors internal and external to the module. **In most cases**, the power limitations of the gate resistors will limit the module power.

**Table 8 • Status Output**

Description	Min	Typ	Max	Units
Status output high, status is faulted	3.15	3.3	3.45	V
Status output low, status is OK	0.8			V
Status output impedance high or low	950	1000	1100	$\Omega$

**Table 9 • Reset Input**

Description	Min	Typ	Max	Units
Reset input low—dis-assert reset	-0.5	0	1.0	V
Reset input high—assert reset	2.5	3.3	3.45	V
Input pull-down resistance	1000	1100	1200	$\Omega$

**Table 10 • Digital RS422 Inputs**

Description	Min	Typ	Max	Units
Common mode input range	-0.5		5.5	V
Differential voltage threshold		0.050	0.200	V
Differential impedance	84	92	100	$\Omega$
Common mode impedance	240	255	270	$\Omega$
Common mode Thevenin voltage	1.5	1.65	1.8	V

## 5.4 Board Mounting

The board has two #6 mounting screws. These provide mounting and AC grounding for the controls. The screws are optional but **AC ground should always be used to limit the common mode voltage on the RS422 control interface**. They direct switching currents from the isolation interface to the chassis. Without the screws, the currents are directed through the signal input and power cable. This results in much higher emissions and may interfere with control.

## 5.5 Quickstart

The basic functionality of the board can be tested without a module or DC bus power. To do this the desaturation protection circuitry must first be disabled using jumpers.

To test the board without a module proceed as follows:

- Set switch 2 and switch 3 ON. This selects 80 kHz self-clocking mode. The dead time switches (4–8) will be in effect.
- Connect the source-to-drain at the high and low side gate drive pins. See [Desat Jumper Locations \(see page 15\)](#) for the location of these jumpers. This is to prevent triggering the desaturation circuitry.
- Apply 11 V–13 V power at J2. The loading should be approximately 0.18 A without FETs. With FETs there is the additional power required for the gates.

The gate drive can then be observed at the module input. The procedure is the same if a module is installed except the jumpers are not needed.

### 5.5.1 Full Setup with a Module and DC Bus Power

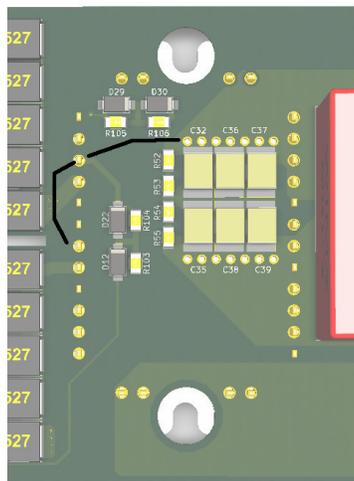
When switching with a module and with DC bus power switching currents are driven from the output devices back into the low voltage signaling environment by capacitive coupling from the high side switch. C8 and C9 are intended to direct these currents back to the DC switching environment and bypass the signal input cable. The following is recommended:

- Mount the board with metal screws on the control side. Their use is highly recommended if control through J1 is used.
- Select the gate resistors as required.
- Set the configuration switches as desired. See [Configuration Switch Settings \(see page 10\)](#).
- Reference [section 3.6 \(see page 4\)](#) for recommendations on connecting power.

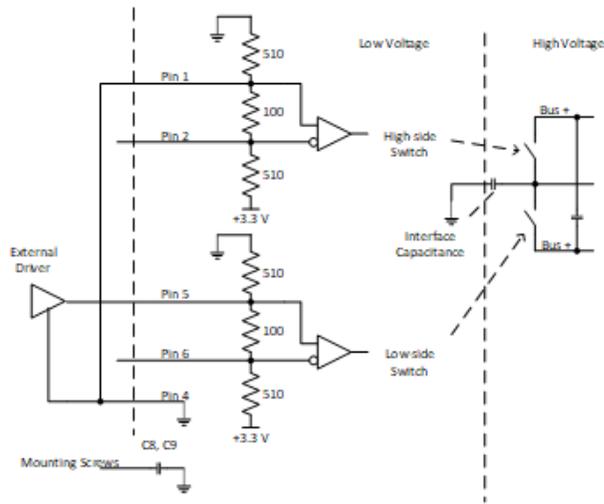
It will be assumed as an example here that testing of the low side switch will be done with the high side OFF. The following input connection figures show the recommended setup. By grounding pin 1, the voltage margin on the upper receiver is doubled. This is recommended if a cable is attached on pins 1 and 2 but should not be necessary if there is no connection at J1. Pin 6 is open. The input at pin 5 should cross the threshold at about 3.3 V.

If noise problems are encountered placing capacitors between pins 1 and 2 and between pins 5 to 6 should help. Also placing a common mode choke on the cable will help direct currents through C8 and C9. If a differential pulse generator is used it is still recommended that pin 4 connect to the pulse generator ground in order to control the common mode input voltage range.

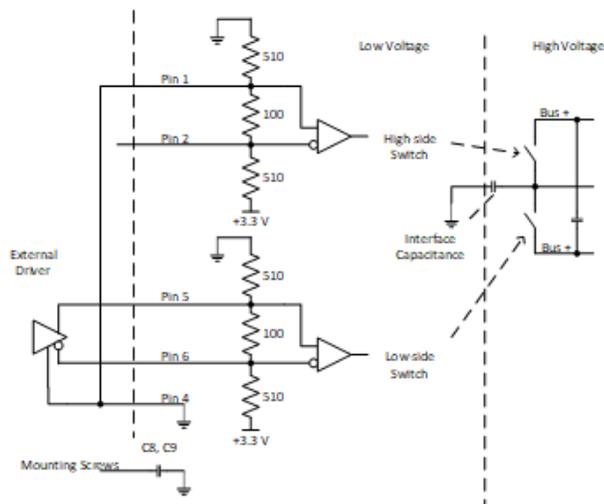
**Figure 6 • Desat Jumper Locations**



**Figure 7 • Singled-ended Input Connection**



**Figure 8 • Differential Input Connection**



## 6 Bill of Materials

The following table shows the bill of materials for the SP3 driver reference designs.

**Table 11 • Bill of Materials**

Reference	Manufacturer	Part Number	Description	QTY
C10	Würth Electronics Inc.	865060445005	CAP 100 $\mu$ F 20% 25 V	1
C11	Samsung Electro-Mechanics America, Inc.	CL10B105KA8NNNC	CAP CER 1 $\mu$ F 25 V X7R 0603	1
C13	Murata Electronics North America	GRM188R61E225KA12D	CAP CER 2.2 $\mu$ F 25 V X5R 0603	1
C14 C74	Samsung Electro-Mechanics	CL21C241JBANNNC	CAP CER 240 pF 50 V COG/NPO 0805	2
C8 C9 C16 C18 C20 C28 C76 C78 C84 C88	KEMET	C0805C104M5RACTU	CAP CER 0.1 $\mu$ F 50 V X7R 0805	10
C19 C79	Nichicon	UCM1H101MCL1GS	CAP ALUM 100 $\mu$ F 20% 50 V SMD	2
C1–C2	KEMET	C0805C101K3GACTU	CAP CER 100 pF 25 V 10% NPO 0805	2
C21 C23 C81 C83	Taiyo Yuden	UMK316BBJ106ML-T	CAP CER 10 $\mu$ F 50 V X5R 1206	4
C22 C25 C27 C82 C85 C87	Taiyo Yuden	UMK325AB7106MM-T	CAP CER 10 $\mu$ F 50 V X7R 1210	6
C24 C41 C49	Taiyo Yuden	TMK107B7105KA-T	CAP CER 1 $\mu$ F 25 V X7R 0603	3
C26 C86 C15 C75	TDK Corporation	C2012C0G1E103J060AA	CAP CER 10000 pF 25 V COG 0805	4
C29 C31	WIMA	DCP4R251007HD4KYS	Film Capacitors 10 $\mu$ F 1300 V 10% 4 LD 24 $\times$ 45.5 $\times$ 41.5 PCM 37.5	2
C3	Taiyo Yuden	TMK212BBJ106KG-T	CAP CER 10 $\mu$ F 25 V X5R 0805	1
C30 C34	Murata Electronics North America	GRM188R71E104JA01J	CAP CER 0.1 $\mu$ F 25 V X7R 0603	2
C32 C35–C40 C42–C48	TDK Corporation	CKG57NX7T2J105M500JH	CAP CER 1 $\mu$ F 630 V X7T SMD	14
C4	Murata Electronics North America	GRM21BR71E104KA01L	CAP CER 0.1 $\mu$ F 25 V X7R 0805	1
C5	KEMET	C0805C334K5RACTU	CAP CER 0.33 $\mu$ F 50 V X7R 0805	1
C50–C51	KEMET	C0603X103G5JAC7867	CAP CER 10000 pF 50 V U2J 0603	2
C52–C53	Panasonic Electronic Components	EEE-FTH101XAP	CAP ALUM 100 $\mu$ F 20% 50 V SMD	2
C54–C57	Yageo	CC0805JRX7R8BB104	CAP CER 0.1 $\mu$ F 25 V X7R 0805	4
C6	KEMET	C0805C103K5RACTU	CAP CER 10000 pF 50 V X7R 0805	1
C7 C12 C89 C91	Nichicon	UUD1H100MCL1GS	CAP ALUM 10 $\mu$ F 20% 50 V SMD	4
C90 C92	Würth Electronics Inc.	885012209019	CAP CER 0.1 $\mu$ F 25 V X7R 1210	2
D1	ON Semiconductor	MMBD7000LT1G	DIODE ARRAY GP 100 V 200 mA SOT23	1
D10 D19–D20 D31–D32 D9	Rohm Semiconductor	RB520CM-60T2R	DIODE SCHOTTKY 60 V 100 mA VMN2M	6
D11 D21	Diodes Incorporated	DDZ4V7ASF-7	DIODE ZENER 4.56 V 500 MW SOD323F	2
D13 D23	ON Semiconductor	SZBZX84C4V7LT1G	DIODE ZENER 4.7 V 225 MW SOT23-3	2
D14–D17 D24– D27	Vishay Semiconductor Diodes Division	SS3P4-M3/84A	DIODE SCHOTTKY 40 V 3 A DO220AA	8

Reference	Manufacturer	Part Number	Description	QTY
D28	OSRAM Opto Semiconductors Inc.	LY T67K-K2M1-26-Z	LED YELLOW CLEAR 2PLCC SMD	1
D2-D5	OSRAM Opto Semiconductors Inc.	LG T67K-H2K1-24-Z	LED GREEN CLEAR 2PLCC SMD	4
D6	OSRAM Opto Semiconductors Inc.	LS T67F-T2V2-1-1-Z	LED RED CLEAR 2PLCC SMD	1
D7	OSRAM Opto Semiconductors Inc.	LO T67K-K1L2-24-Z	LED ORANGE CLEAR 2PLCC SMD	1
D8 D18	Comchip Technology	CDBHD240-G	DIODE BRIDGE 2 A 40 V TO-269AA	2
J1	Wurth Electronics Inc.	61200821721	CONN HEADER 8 POS RA 2.54	1
J2	On Shore Technology Inc.	OSTVN02A150	CONN TERM BLOCK 2.54 mm 2POS PCB	1
J3	On Shore Technology Inc.	302-S101	CONN HEADER VERT 10POS GOLD	1
J4-J6	Wurth Electronics Inc.	74650094R	BUSH, THR OPENM4, THR 3.0 mm	3
L1-L2	Murata Electronics North America	DLP11SN201HL2L	CMC 110MA 2LN 200 Ω SMD	2
L3 L5	J.W. Miller	PM54-220M-RC	Fixed Inductors 22 μH 20%	2
L4 L6	Bourns Inc.	SDR1005-101KL	FIXED IND 100 μH 1 A 330 MΩ SMD	2
PS1	STMicroelectronics	LD1086DT33TR	IC REG LDO 3.3 V 1.5 A DPAK	1
PS2	Texas Instruments	LM3480IM3-3.3/NOPB	IC REG LINEAR 3.3 V 100 mA SOT23-3	1
Q1	ON Semiconductor	BSS138L	MOSFET N-CH 50 V 0.2 A SOT-23	1
R1 R3 R5 R7	Stackpole Electronics Inc.	RMCF0805FT510R	RES SMD 510 Ω 1% 1/8 W 0805	4
R102	Panasonic Electronic Components	ERJ-PA3J751V	RES SMD 750 Ω 5% 1/4 W 0603	1
R11	Stackpole Electronics Inc.	RMCF0805FT10R0	RES SMD 10 Ω 1% 1/8 W 0805	1
R12	Stackpole Electronics Inc.	RMCF0805JT10K0	RES SMD 10K Ω 5% 1/8 W 0805	1
R13-R14	Stackpole Electronics Inc.	RNCP0603FTD20K0	RES SMD 20K Ω 1% 1/8 W 0603	2
R15-R18	Panasonic Electronic Components	ERJ-6ENF1500V	RES SMD 150 Ω 1% 1/8 W 0805	4
R19-R20	Stackpole Electronics Inc.	RMCF0603JT1K00	RES SMD 1K Ω 5% 1/10 W 0603	2
R2 R4 R6 R8	Stackpole Electronics Inc.	RMCF0805FT51R0	RES SMD 51 Ω 1% 1/8 W 0805	4
R21	Yageo	RC0603FR-0714K3L	RES SMD 14.3K Ω 1% 1/10 W 0603	1
R22	Panasonic Electronic Components	ERJ-PA3F1500V	RES SMD 150 Ω 1% 1/4 W 0603	1
R23 R68	Yageo	RC0805FR-07110KL	RES SMD 110K Ω 1% 1/8 W 0805	2
R24 R69	Stackpole Electronics Inc.	RNCP0805FTD180R	RES SMD 180 Ω 1% 1/4 W 0805	2
R25 R70	Stackpole Electronics Inc.	RNCP0805FTD100R	RES SMD 100 Ω 1% 1/4 W 0805	2
R26-R27 R30 R71-R72 R75	Stackpole Electronics Inc.	RNCP1206FTD10R0	RES SMD 10 Ω 1% 1/2 W 1206	6
R28 R73	Susumu	KRL1632E-M-R100-F-T5	RES 0.1 Ω 1% 3/4 W 1206	2
R31 R76	Stackpole Electronics Inc.	RNCP1206FTD10K0	RES SMD 10K Ω 1% 1/2 W 1206	2
R32 R77	Stackpole Electronics Inc.	RMCF0805JT220R	RES SMD 220 Ω 5% 1/8 W 0805	2
R33 R78	Stackpole Electronics Inc.	RMCP2010FT47R0	RES SMD 47 Ω 1% 1 W 2010	2
R35 R80	Stackpole Electronics Inc.	RNCP0805FTD2K00	RES SMD 2K Ω 1% 1/4 W 0805	2
R36 R81	Stackpole Electronics Inc.	RMCF1206FT4K70	RES SMD 4.7K Ω 1% 1/4 W 1206	2
R38 R83	Yageo	RC0805FR-072KL	RES SMD 2K Ω 1% 1/8 W 0805	2
R39 R84	Panasonic Electronic Components	ERJ-6ENF2152V	RES SMD 21.5K Ω 1% 1/8 W 0805	2
R40-R45 R85-R90	Bourns Inc.	CRM2512-FX-10R0ELF	RES SMD 10 Ω 1% 2 W 2512	12
R46 R91	Stackpole Electronics Inc.	RMCF1206FT1K24	RES SMD 1.24K Ω 1% 1/4 W 1206	2

Reference	Manufacturer	Part Number	Description	QTY
R47 R64–R65	Stackpole Electronics Inc.	RNCP0603FTD10K0	RES SMD 10K $\Omega$ 1% 1/8 W 0603	3
R52–R63	Yageo	RV1206FR-071ML	RES SMD 1M $\Omega$ 1% 1/4 W 1206	12
R66	Vishay Dale	RCS0603100KFKEA	RES SMD 100K $\Omega$ 1% 1/4 W 0603	1
R67	Vishay Thin Film	PNM0603E5001BST5	RES SMD 5K $\Omega$ 0.1% 0.15 W 0603	1
R94	Panasonic Electronic Components	ERJ-3EKF10R0V	RES SMD 10 $\Omega$ 1% 1/10 W 0603	1
R95	Vishay Beyschlag	MCT06030C1003FP500	RES SMD 100K $\Omega$ 1% 1/8 W 0603	1
R96 R99	Vishay Beyschlag	MCT06030D1003DP500	RES SMD 100K $\Omega$ 0.5% 1/8 W 0603	2
R97 R100	Vishay Dale	TNPW06033K00BEEA	RES 3K $\Omega$ 0.1% 1/8 W 0603	4
R98 R101	Yageo	RC0603FR-07100RL	RES SMD 100 $\Omega$ 1% 1/10 W 0603	4
R9–R10	Stackpole Electronics Inc.	RMCF0805JT1K00	RES SMD 1K $\Omega$ 5% 1/8 W 0805	2
S1	TE Connectivity ALCOSWITCH Switches	4-1825059-1	Dip Switch SPST 8 Position Surface Mount Slide (Standard) Actuator 100 mA 24 VDC	1
TP1 TP5	Keystone Electronics	5001	TEST POINT PC MINI .040D black	2
TP2	Keystone Electronics	5004	TEST POINT PC MINI .040D black	1
TP3 TP6 TP9	Keystone Electronics	5003	TEST POINT PC MINI .040D black	3
TP4 TP7–TP8	Keystone Electronics	5002	TEST POINT PC MINI .040D black	3
U1	Texas Instruments	AM26LV32CDR	IC QUAD DIFF LINE RCVR 16-SOIC	1
U11	Maxim Integrated	MAX9019EKA+T	IC COMPARATOR DUAL SOT23-8	1
U12	Texas Instruments	ISO7810DW	DGTL ISO 5.7 kV GEN PURP 16SOIC	1
U16	Analog Devices Inc.	ADUM4135BRWZ	DGTL ISO 5 kV 1CH GATE DVR 16SOIC	1
U19–U20	Texas Instruments	TPS3710DDCT	SUPERVISORY CIRCUITS WIDE VIN	2
U2	Microsemi Corporation	AGL030V2-VQG100	IC FPGA 77 I/O 100VQFP	1
U3	Linear Technology	LT3007ITS8-1.5 #TRMPBF	IC REG LDO 1.5 V 20 mA TSOT23-8	1
U4 U13	Texas Instruments	UCC28089DR	IC REG CTRLR PUSH-PULL 8SOIC	2
U5–U6 U14–U15	Fairchild/ON Semiconductor	FDS3512	MOSFET N-CH 80 V 4 A 8SOIC	4
U7	Analog Devices Inc.	ADUM4136BRWZ	DGTL ISO 5 kV 1CH GATE DVR 16SOIC	1
U8 U17	Linear Technology	LT1171HVCQ#PBF	IC REG MULT CONFIG INV ADJ 5DDPAK	2
U9 U18	IXYS Integrated Circuits Division	IXDD630MYI	IC GATE DRIVER LOW SIDE TO-263-5	2
Y1	Epson	SG-636PCE	OSC XO 10.000 MHz CMOS SMD	1
T1 T2	Epcos	B65814N1012D002	Coil Form	2
T1 T2	Epcos	B65813J0000R041	5.5 $\mu$ H, N41 RM10 Core	2
T1 T2	Epcos	B65814B2203X000	RM10 Core Clip	4
T1 T2	Belden	8077	Approximately 4 ft., 22 ga. wire	
D29/30 D12/22	Sanken	RP 1HV1	DIODE 2 kV 100 mA	2

# 7 Schematics

The following illustrations show the schematics of the MSCSICSP3/REF2 device.

Figure 9 • SELV/Control Schematic

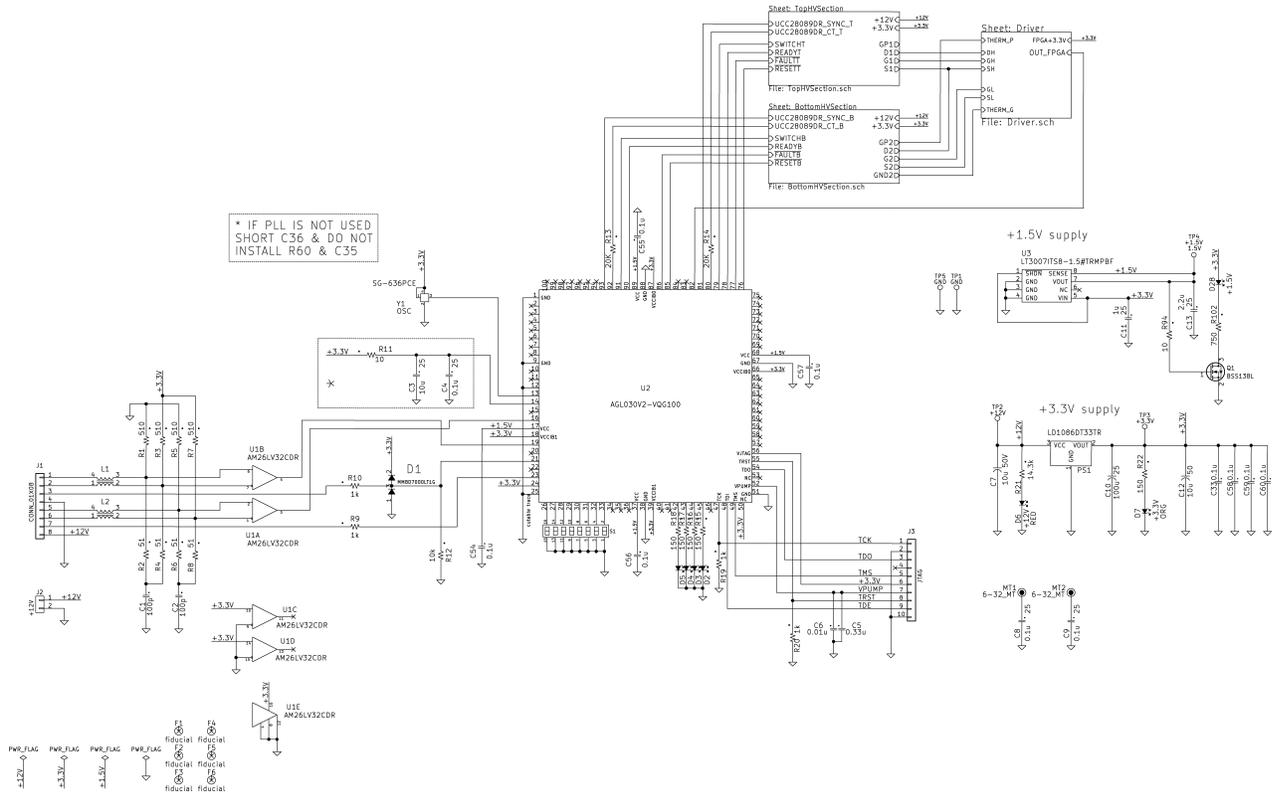


Figure 10 • Bottom-side Driver Schematic

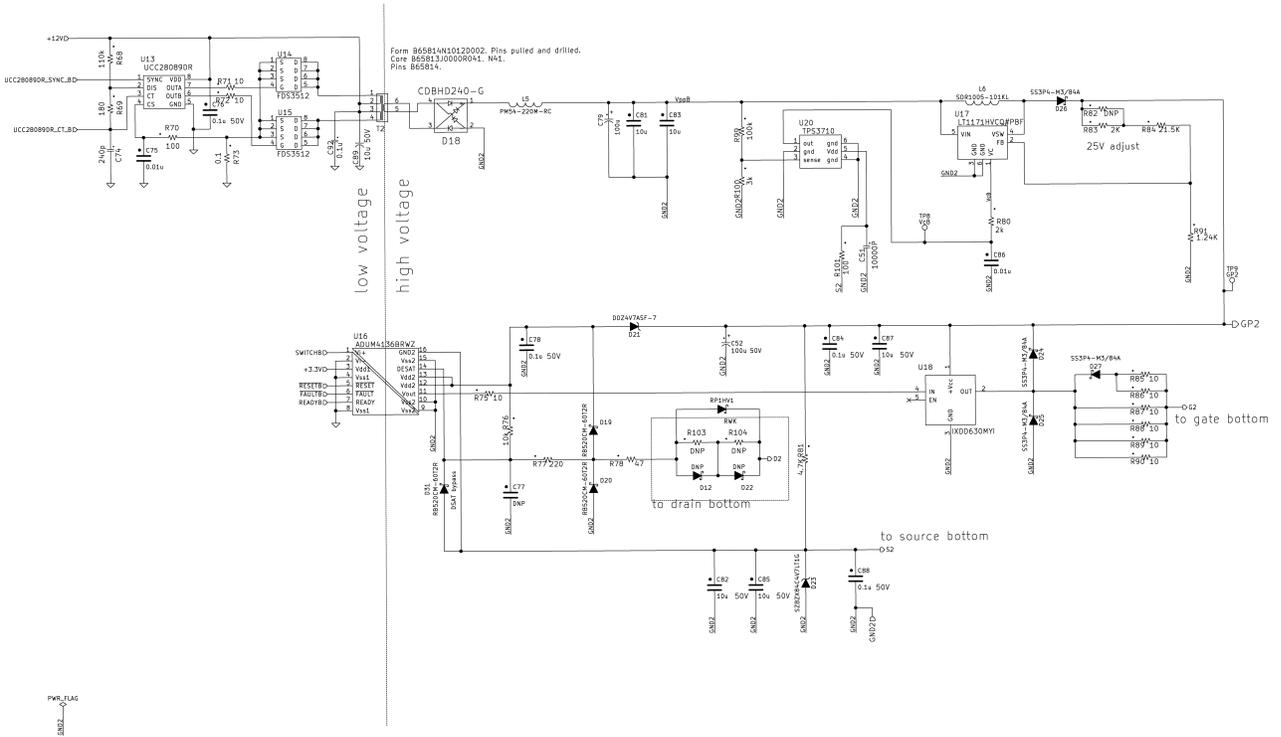
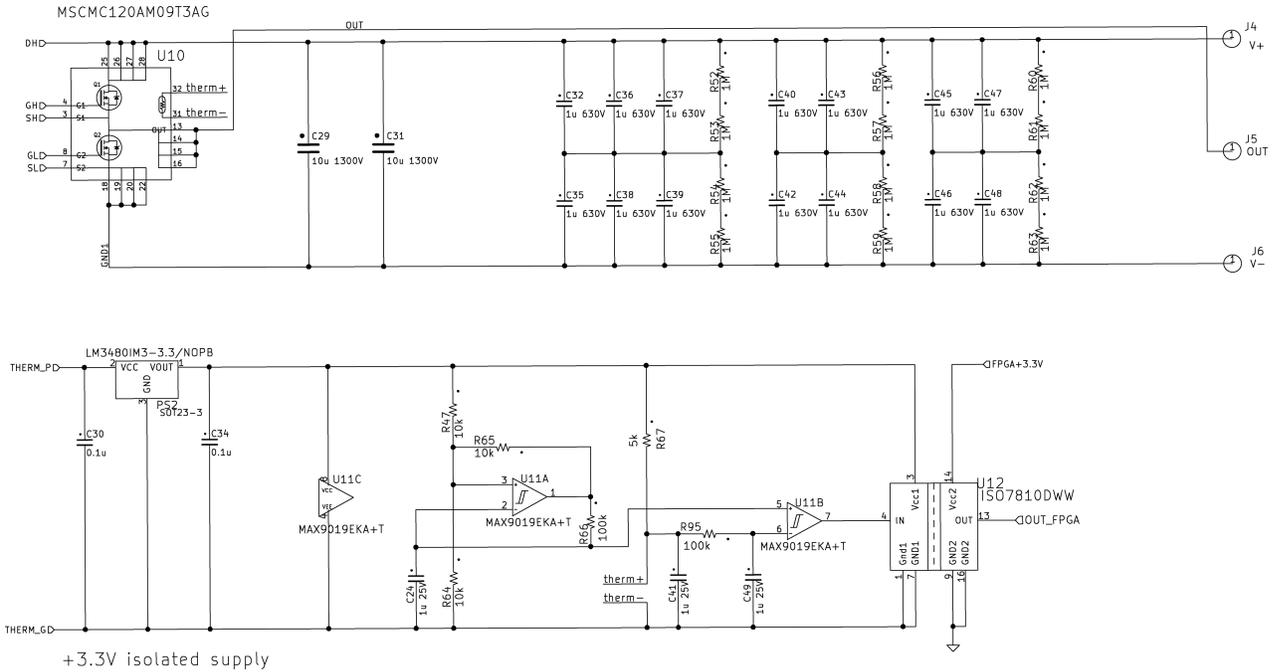


Figure 11 • Power-side and Low-side Thermistor Schematic





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